**Product data sheet** 

### 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Trench MOSFET technology
- Leadless ultra small and ultra thin SMD plastic package: 1.0 × 0.6 × 0.37 mm
- ElectroStatic Discharge (ESD) protection > 1 kV HBM
- Drain-source on-state resistance R<sub>DSon</sub> = 1.02 Ω

# 3. Applications

- Relay driver
- High-speed line driver
- · High-side load switch
- Switching circuits

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
V <sub>GS</sub>	gate-source voltage			-8	-	8	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-500	mA
Static characte	Static characteristics						
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -500 mA; $T_j$ = 25 °C		-	1.02	1.4	Ω

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.





# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D I
2	S	source	2 3	
3	D	drain	Transparent top view  DFN1006B-3 (SOT883B)	G S S 017aaa259

# 6. Ordering information

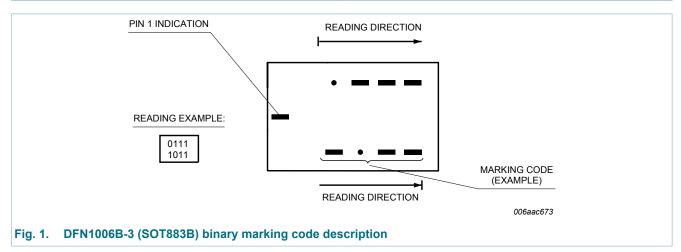
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PMZB950UPE	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
PMZB950UPE	0101 1001



# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-8	8	V
I <sub>D</sub>	drain current	$V_{GS}$ = -4.5 V; $T_{amb}$ = 25 °C	[1]	-	-500	mA
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-300	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	-2	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	360	mW
			[1]	-	715	mW
		T <sub>sp</sub> = 25 °C		-	2700	mW
Tj	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-dra	in diode		'	'	'	
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-350	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

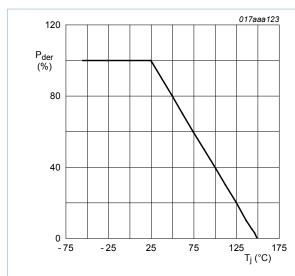


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

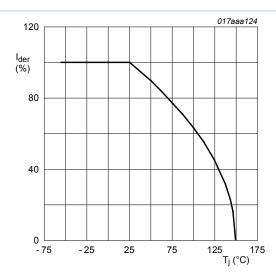


Fig. 3. Normalized continuous drain current as a function of junction temperature

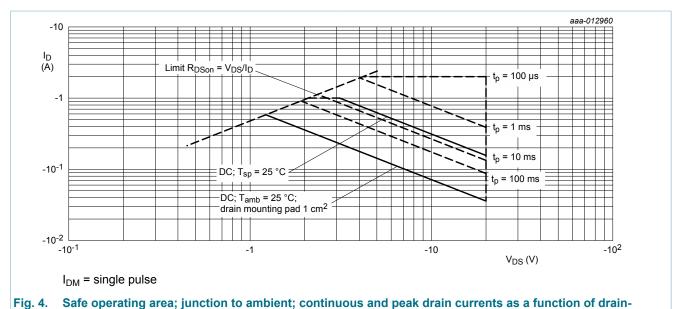
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

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#### 20 V, P-channel Trench MOSFET



# source voltage

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
uig-a)	thermal resistance from junction to ambient		[1]	-	305	360	K/W
			[2]	-	150	175	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	-	40	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm<sup>2</sup>.

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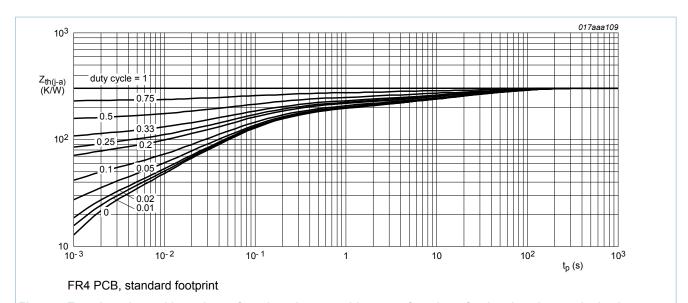


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

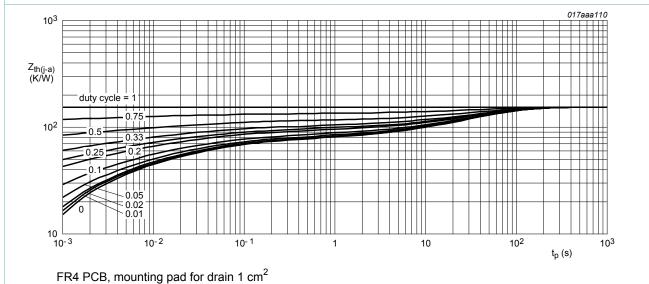


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

# 10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics		'			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C	-0.45	-0.7	-0.95	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
		V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C	-	-	-10	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 8 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-10	μΑ
		V <sub>GS</sub> = -4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μA
		V <sub>GS</sub> = 4.5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -500 mA; $T_j$ = 25 °C	-	1.02	1.4	Ω
	resistance	V <sub>GS</sub> = -4.5 V; I <sub>D</sub> = -500 mA; T <sub>j</sub> = 150 °C	-	1.54	2.1	Ω
		$V_{GS}$ = -2.5 V; $I_D$ = -200 mA; $T_j$ = 25 °C	-	1.27	2.2	Ω
		$V_{GS}$ = -1.8 V; $I_D$ = -40 mA; $T_j$ = 25 °C	-	1.7	3.3	Ω
		$V_{GS}$ = -1.5 V; $I_D$ = -10 mA; $T_j$ = 25 °C	-	2.3	5	Ω
		$V_{GS}$ = -1.2 V; $I_D$ = -1 mA; $T_j$ = 25 °C	-	3.5	-	Ω
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -500 mA; $T_{j}$ = 25 °C	-	480	-	mS
Dynamic cl	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = -10 V; I <sub>D</sub> = -450 mA;	-	1.19	2.1	nC
$Q_{GS}$	gate-source charge	$V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$	-	0.17	-	nC
$Q_{GD}$	gate-drain charge		-	0.1	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = -10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	43	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	14	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	8	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -0.45 A; $R_{L}$ = 22 $\Omega$ ;	-	2.3	-	ns
t <sub>r</sub>	rise time	$V_{GS} = -4.5 \text{ V}; R_{G(ext)} = 6 \Omega; T_j = 25 \text{ °C}$	-	5	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	13.5	-	ns
t <sub>f</sub>	fall time		-	6	-	ns
Source-dra	in diode		l l	1	1	J
$V_{SD}$	source-drain voltage	$I_S$ = -115 mA; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-	-0.7	-1.2	V

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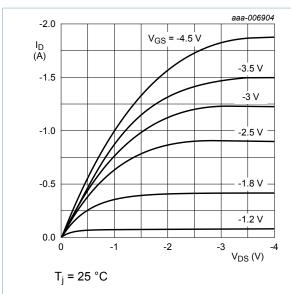


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

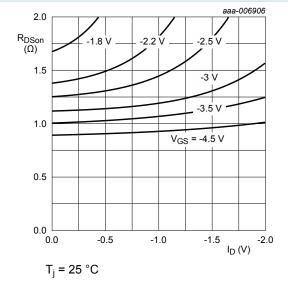


Fig. 9. Drain-source on-state resistance as a function of drain current; typical values

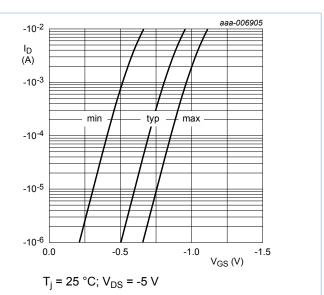


Fig. 8. Sub-threshold drain current as a function of gate-source voltage

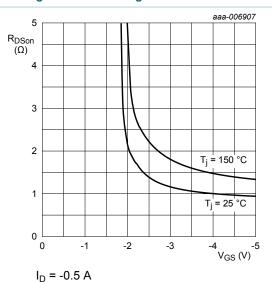


Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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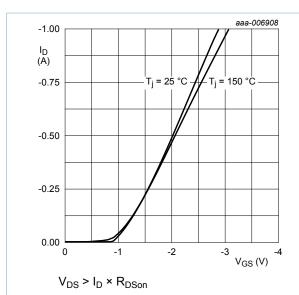


Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

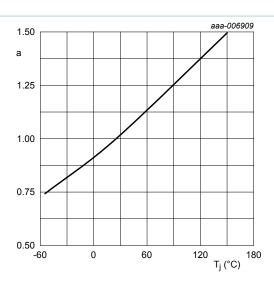


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

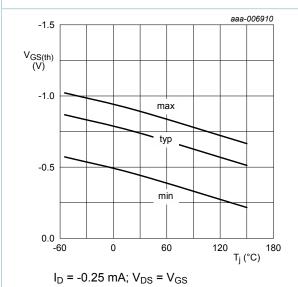


Fig. 13. Gate-source threshold voltage as a function of junction temperature

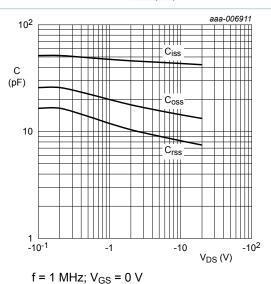


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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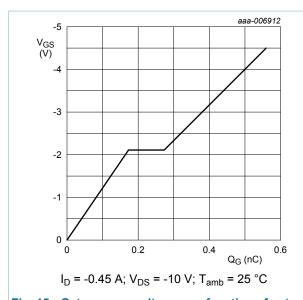


Fig. 15. Gate-source voltage as a function of gate charge; typical values

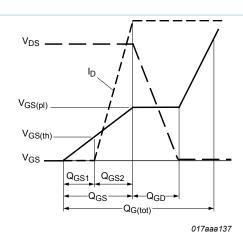


Fig. 16. MOSFET transistor: Gate charge waveform definitions

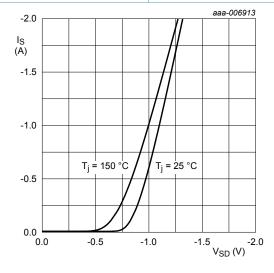
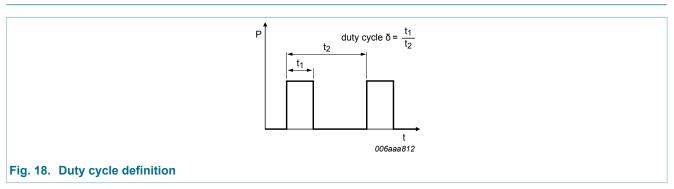


Fig. 17. Source current as a function of source-drain voltage; typical values

### 11. Test information

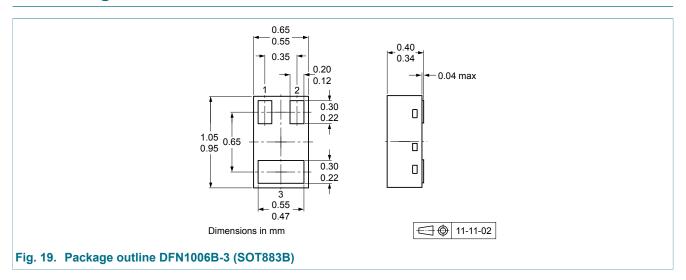
 $V_{GS} = 0 V$ 



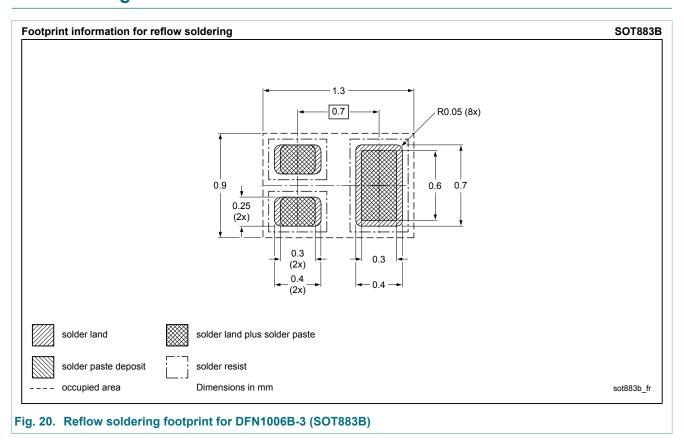
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# 12. Package outline



# 13. Soldering



# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMZB950UPE v.1	20140728	Product data sheet	-	-

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Document status [1][2]	Product status [3]	Definition
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Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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